

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	69813	capacitor near3 (form or forming or formation or fabrication)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 16:53
L2	2148965	threshold voltage or Vt or "V.sub.t "	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 16:59
L3	257298	l2 near4 (shift or change or changing or altering of affect or effect or affecting)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 16:59
L4	12230	l1 and l3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 16:57
L5	8478441	high k or high dielectric constant or high kappa or tantalum oxide or "Ta.sub.2 O.sub.5 "	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 17:00
L6	135120	threshold voltage or Vt or "V.sub.t "	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	ADJ	ON	2005/02/01 16:59
L7	17279	l6 near4 (shift or change or changing or altering of affect or effect or affecting)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 16:59
L8	1156	l1 and l7	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 16:59
L9	40266	high k or high dielectric constant or high kappa or tantalum oxide or "Ta.sub.2 O.sub.5 "	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	ADJ	ON	2005/02/01 17:00
L10	156	l8 and l9	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	ADJ	ON	2005/02/01 17:00

L11	78	barrier layer near6 l6	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	ADJ	ON	2005/02/01 17:00
L12	3	110 and 111	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	ADJ	ON	2005/02/01 17:00

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